

200mW High Power Laser Diode

Description

The SLD302XT is a gain-guided, high-power laser diode with a built-in TE cooler. A new flat, square package with a low thermal resistance and an in-line pin configuration is employed.

Fine tuning of the wavelength is possible by controlling the laser chip temperature.

Features

- High power
Recommended power output $P_o = 180\text{mW}$
- Low operating current
- Newly developed flat package with built-in TE cooler, thermistor, and photodiode.

Applications

- Solid state laser excitation
- Medical use

Structure

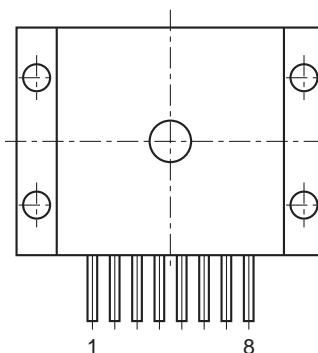
GaAlAs double-hetero-type laser diode

Absolute Maximum Ratings ($T_{th} = 25^\circ\text{C}$)

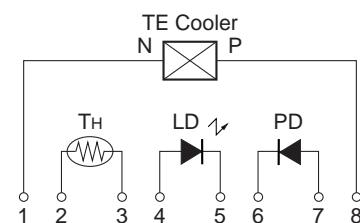
• Optical power output	P_o	200	mW
• Reverse voltage	V_R	LD 2	V
	PD	15	V
• Operating temperature	T_{opr}	-10 to +50	$^\circ\text{C}$
• Storage temperature	T_{stg}	-40 to +85	$^\circ\text{C}$
• Operating current of TE cooler	I_T	2.5	A

Pin Configuration (Top View)

No.	Function
1	TE cooler, negative
2	Thermistor lead 1
3	Thermistor lead 2
4	Laser diode anode
5	Laser diode cathode
6	Photodiode cathode
7	Photodiode anode
8	TE cooler, positive



Equivalent Circuit



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Electrical and Optical Characteristics(T_{th}: Thermistor temperature, T_{th} = 25°C)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Threshold current	I _{th}			150	200	mA
Operating current	I _{op}	P _o = 180mW		350	500	mA
Operating voltage	V _{op}	P _o = 180mW		1.9	3.0	V
Wavelength*1	λ _p	P _o = 180mW	770		840	nm
Monitor current	I _{mon}	P _o = 180mW V _R = 10V		0.3		mA
Radiation angle (F. W. H. M.*)	Perpendicular	θ _⊥	P _o = 180mW	28	40	degree
	Parallel	θ _{//}		12	17	degree
Positional accuracy	Position	ΔX, ΔY	P _o = 180mW		±100	μm
	Angle	Δφ _⊥			±3	degree
Differential efficiency	η _D	P _o = 180mW	0.65	0.9		mW/mA
Thermistor resistance	R _{th}	T _{th} = 25°C		10		kΩ

* F. W. H. M. : Full Width at Half Maximum

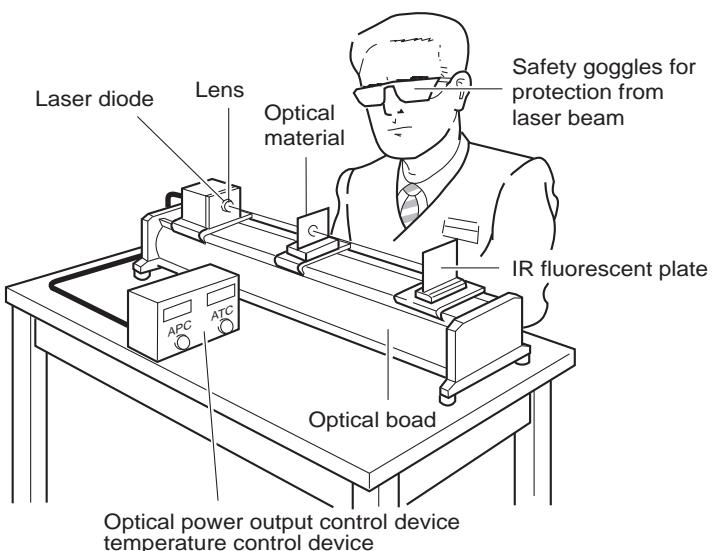
***1 Wavelength Selection Classification**

Type	Wavelength (nm)
SLD302XT-1	785 ± 15
SLD302XT-2	810 ± 10
SLD302XT-3	830 ± 10

Type	Wavelength (nm)
SLD302XT-21	798 ± 3
SLD302XT-24	807 ± 3
SLD302XT-25	810 ± 3

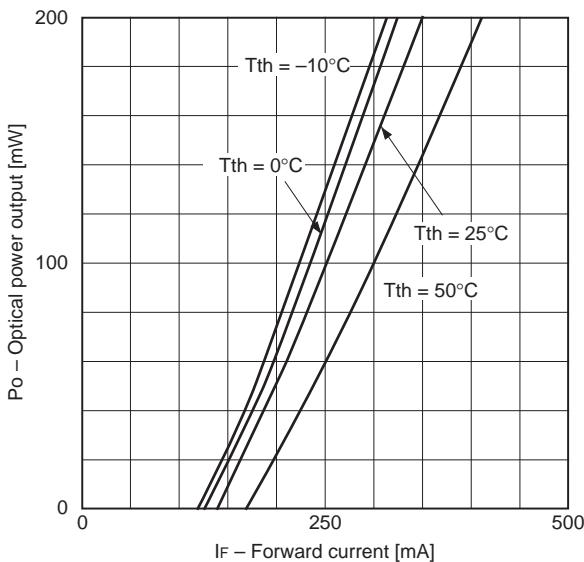
Handling Precautions**Eye protection against laser beams**

The optical output of laser diodes ranges from several mW to 1W. However the optical power density of the laser beam at the diode chip reaches 1mW/cm². Unlike gas lasers, since laser diode beams are divergent, uncollimated laser diode beams are fairly safe at a laser diode. For observing laser beams, ALWAYS use safety goggles that block infrared rays. Usage of IR scopes, IR cameras and fluorescent plates is also recommended for monitoring laser beams safely.

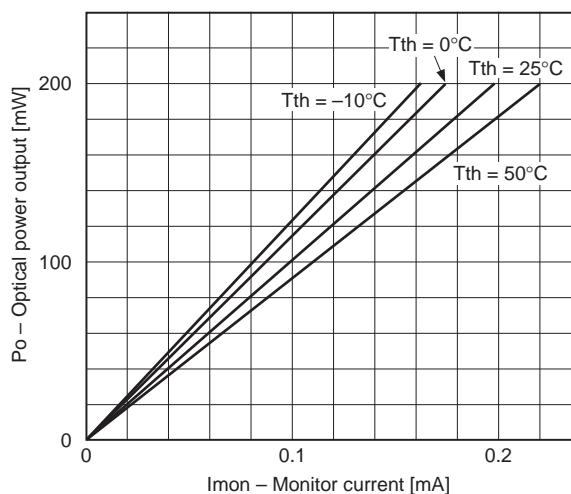


Example of Representative Characteristics

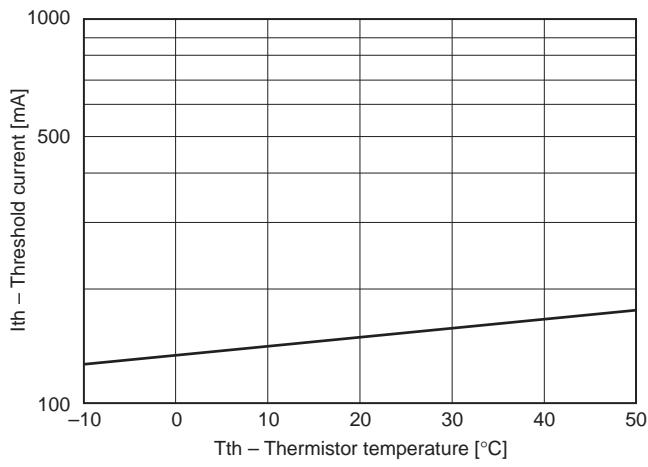
**Optical power output vs.
Forward current characteristics**



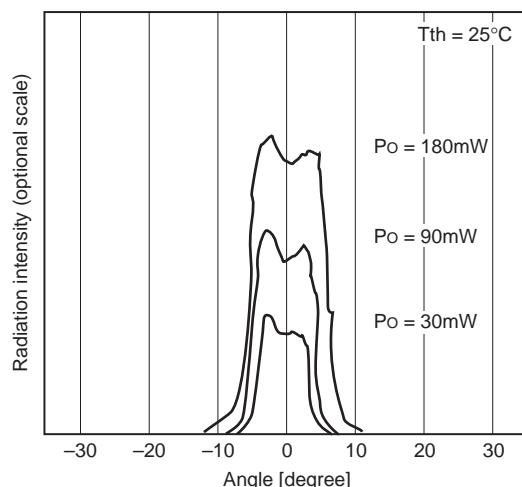
Optical power output vs. Monitor current characteristics



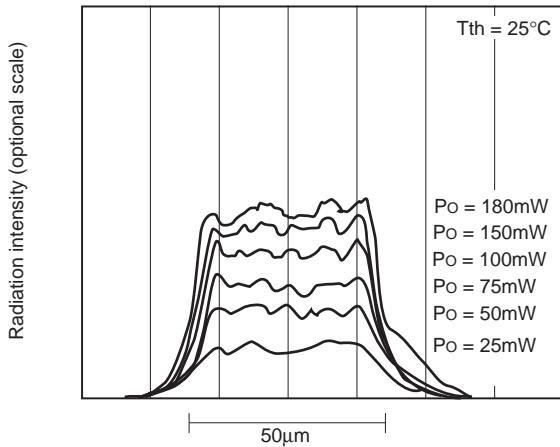
Threshold current vs. Temperature characteristics



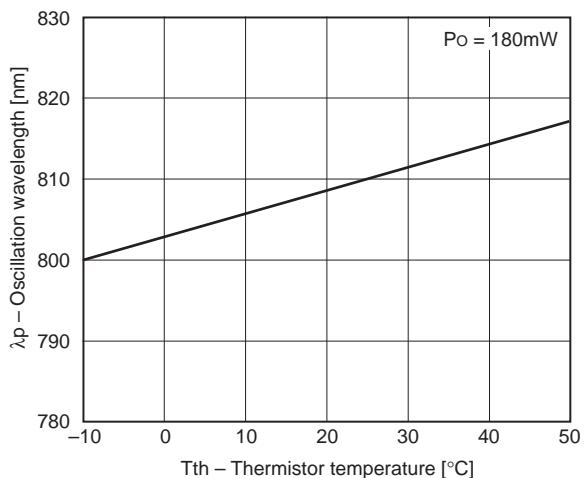
**Power dependence of far field pattern
(parallel to junction)**

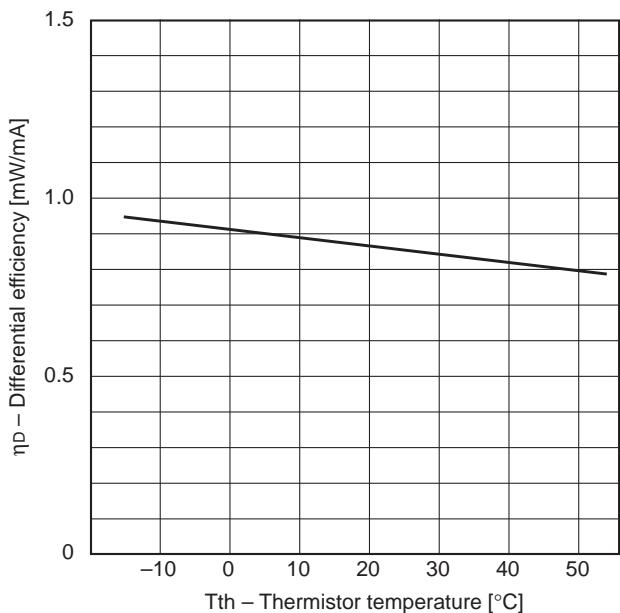
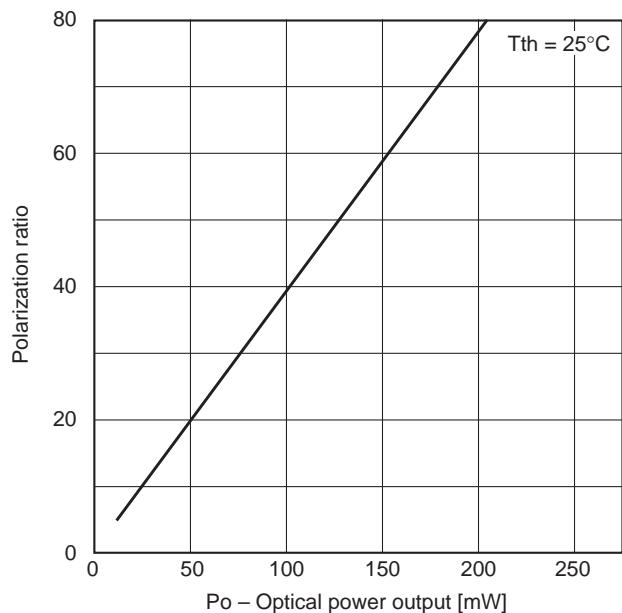


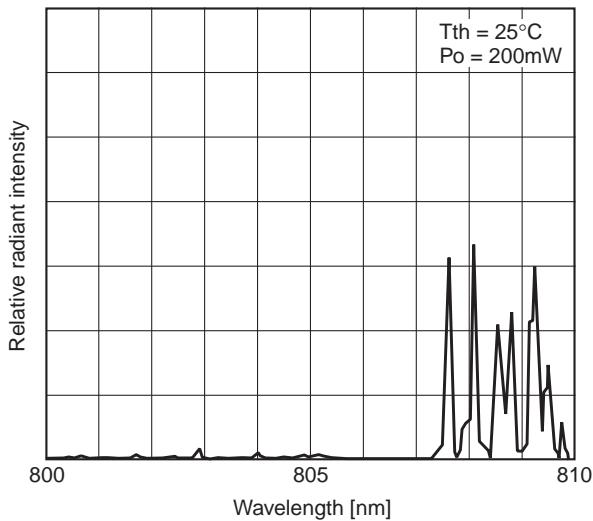
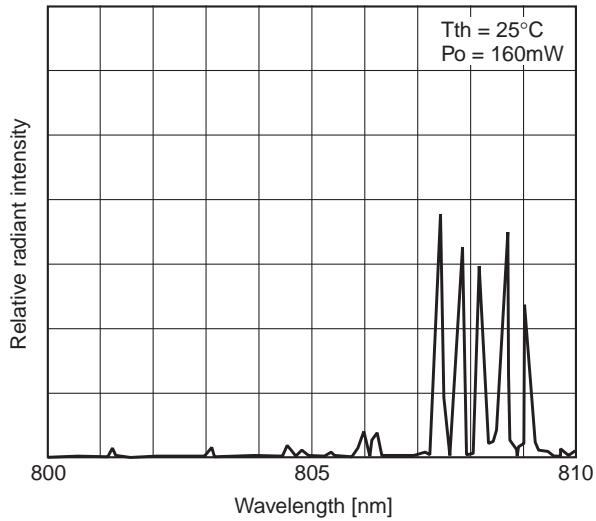
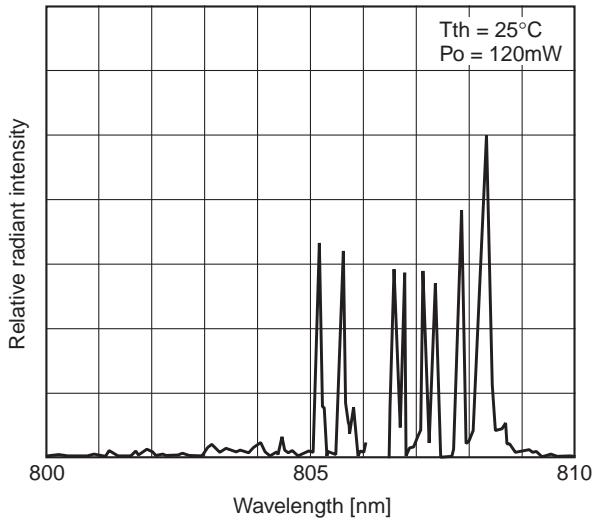
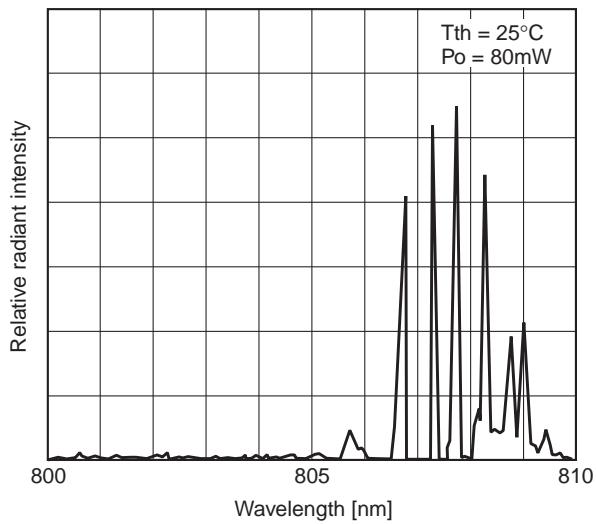
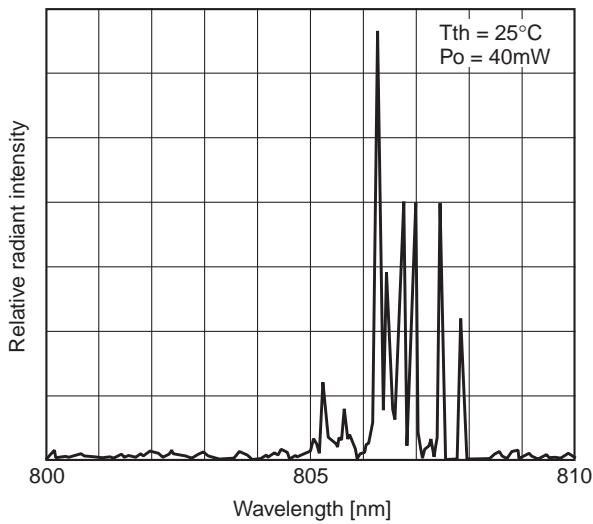
Power dependence of near field pattern

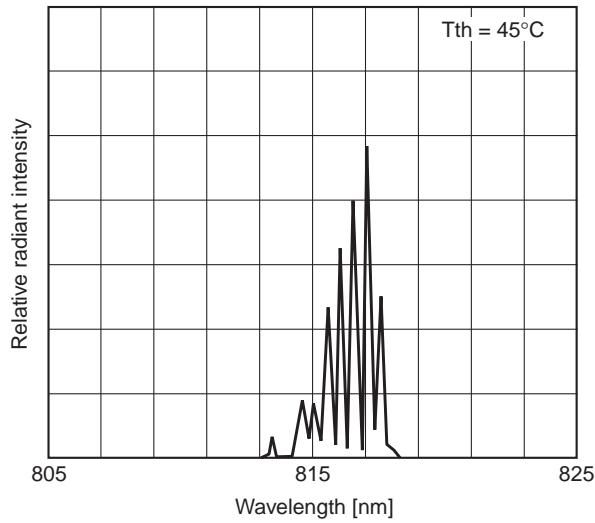
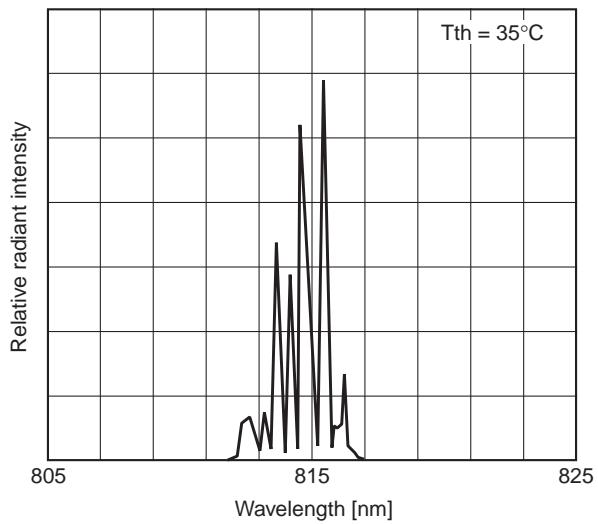
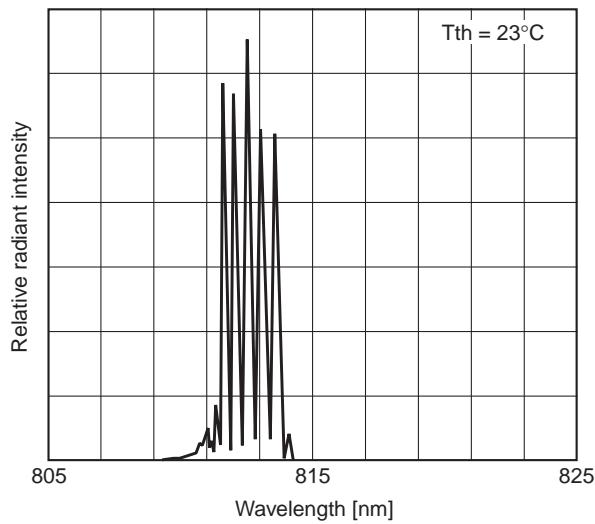
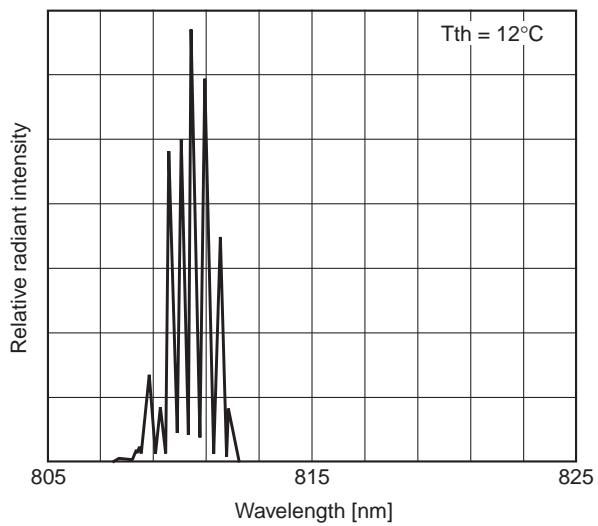
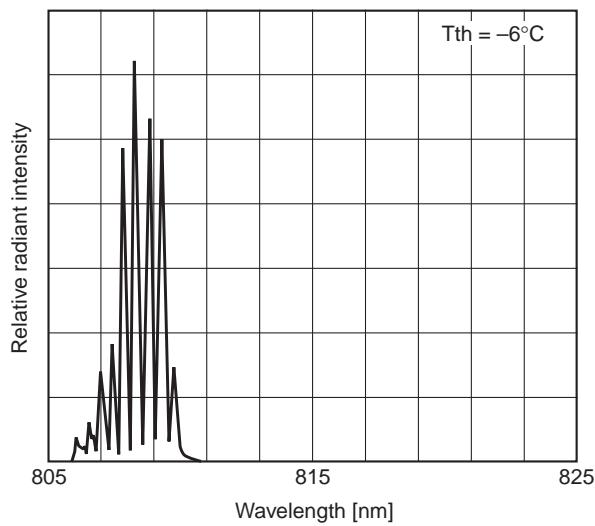


Oscillation wavelength vs. Temperature characteristics

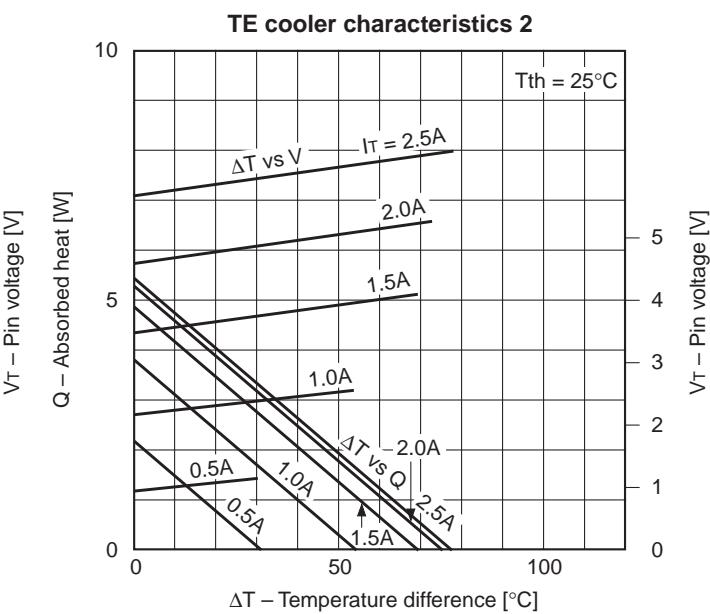
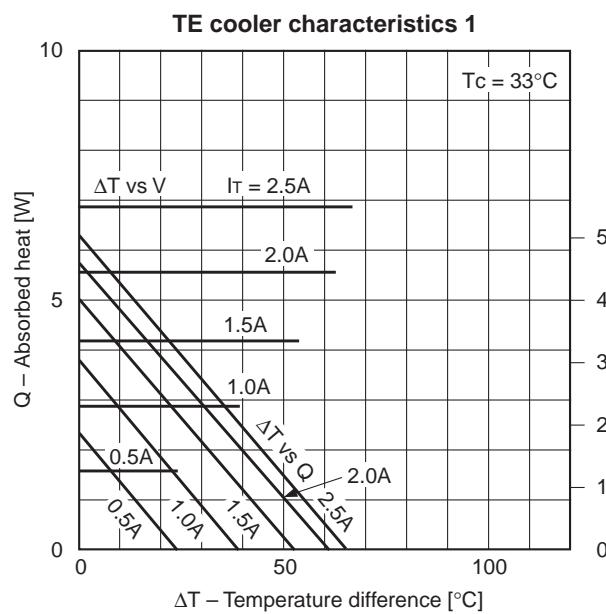


Differential efficiency vs. Temperature characteristics**Power dependence of polarization ratio**

Power dependence of wavelength

Temperature dependence of wavelength ($P_o = 180\text{mW}$)

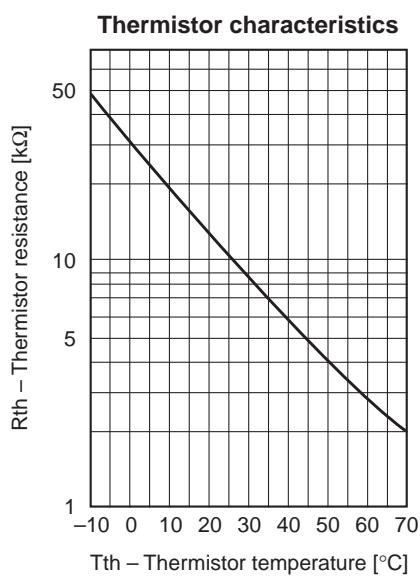
TE cooler characteristics



ΔT : $T_c - T_{th}$

T_{th} : Thermistor temperature

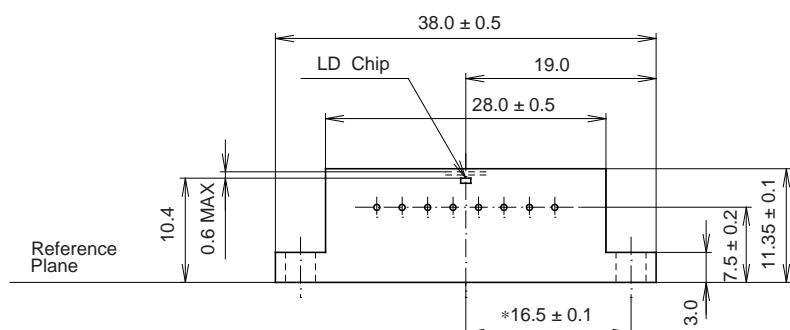
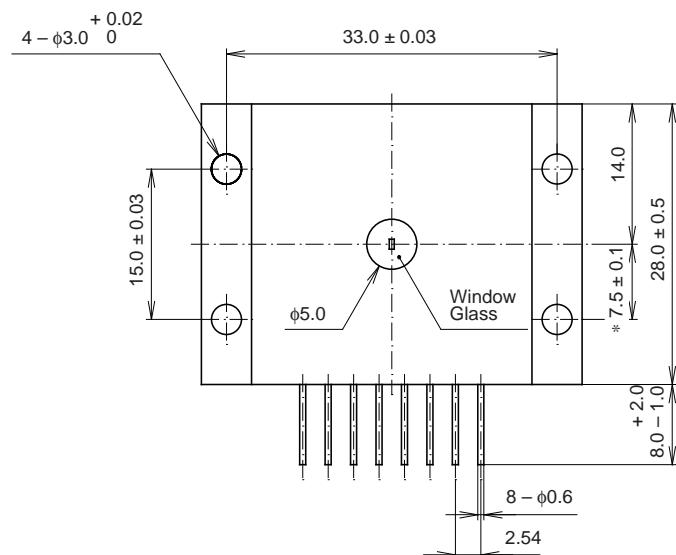
T_c : Case temperature



Package Outline

Unit: mm

M-247 (LO-10)



*Distance between pilot hole and emitting area

SONY CODE	M-247
EIAJ CODE	_____
JEDEC CODE	_____

PACKAGE WEIGHT	4.3g
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